

Spin-orbit coupling and intrinsic spin mixing in quantum dots

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Spin-orbit coupling effects are studied in quantum dots in InSb, a narrow-gap material. Competition between different Rashba and Dresselhaus terms is shown to produce wholesale changes in the spectrum. The large (and negative) g -factor and the Rashba field produce states where spin is no longer a good quantum number and intrinsic spins occur at moderate magnetic fields. For dots with two electrons, a singlet-triplet mixing occurs in the ground state, with observable signatures in intraband FIR absorption, and possible importance in quantum computation.

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The creation and manipulation of spin populations in semiconductors has received a great deal of attention in recent years. Conceptual developments that have motivated these efforts include prominently the Datta-Das proposal for a spin field-effect transistor,¹ based on the Rashba spin-orbit coupling of electrons in a 2DEG,² and the possibility of building quantum computation devices using quantum dots (QDs).³ It is then important for full control of spin- \uparrow mechanisms in nanostructures that all spin-orbit (SO) effects be understood.

There are two main SO contributions in zincblende materials like A_3B_5 : in addition to the structure inversion asymmetry (SIA) caused by the 2D confinement (the Rashba effect), there is also a SO term caused by the bulk inversion asymmetry (BIA) in those structures (the Dresselhaus term).⁵ Notice that additional lateral confinement defining a QD introduces another SIA term with important consequences, as we will see in detail. Although the relative importance of these two effects depends on the materials and structure design (via interfacial fields), only recently have authors begun to consider the behavior of spins under the influence of all effects. For example, a modification of the Datta-Das design was recently suggested to allow for a diusive version of the spin FET,⁴ and that proposal relies on the additional influence of the Dresselhaus SO coupling in the system.

Work in wide-gap materials (mainly GaAs),⁶ uses a unitary transformation on the Hamiltonian of the system,⁷ after which one gets an effective diagonal SO term which incorporates the Rashba effect in a perturbative fashion. That approach is valid since the SO coupling is small in GaAs. However, the approximation is not valid for all of the A_3B_5 structures, as it is the case for InSb, for example, where both SIA and BIA effects are anticipated to be much larger.⁸ In this material, one needs to deal with the full Hamiltonian.

There are just a few works discussing SO effects in narrow-gap nanostructures. Among them, [9] uses $k \cdot p$ theory in InSb QDs in order to include SIA SO terms from both the Rashba field and the lateral confinement which defines the QD. This last SIA term is considered

in [12], and since it is diagonal in the Fock-Darwin (FD) basis no level mixing is found nor expected. In contrast, level mixing events are clearly identified in [9]. Experiments in InSb QDs have explored the FIR response in lithographically defined dots,¹⁰ and PL features of self-assembled dots.¹¹

The goal of this work is to show how important different types of SO couplings are in the spectra of parabolic QDs built in narrow-gap materials such as InSb. We consider the Rashba-SIA diagonal and SIA non-diagonal, as well as the Dresselhaus-BIA terms in the Hamiltonian, and proceed with its full diagonalization, in order to study features of the spectrum as function of magnetic field, dot size, g -factor, and electron-electron interaction. We draw attention to the appearance of strong level anticrossings (mixing) form moderate magnetic fields in typical QDs, and how this phenomenon (and critical field where it occurs) is modified by the BIA terms not considered before.⁹ As the level mixing involves states with different spin, this induces strong intrinsic spin flips in the system, regardless of the strength of the SO coupling, providing an important channel for spin decoherence in these systems. Moreover, measurement of FIR absorption would yield direct access to the coupling constants; i.e., the dispersion of FIR absorption peaks and appearance of additional/split-off features are a direct consequence of the level mixing introduced by SO.

Model. Assuming a heterojunction or quantum well confinement $V(z)$ such that only the lowest z -subband is occupied, the Hamiltonian in the absence of SO interactions for a QD further defined by a lateral parabolic confinement is given by $H_0 = \frac{\hbar^2}{2m} k^2 + V(\rho) + \frac{1}{2} g_B B$, where $k = i\mathbf{r} + e\mathbf{A} = (\sim c)$, and the in-plane vector potential $\mathbf{A} = B(\sin \phi; \cos \phi; 0) = 2$ describes a perpendicular magnetic field $B = Bz$; m is the effective mass in the conduction band,¹⁵ g is the bulk g -factor, μ_B is Bohr's magneton, $V(\rho) = \frac{1}{2} m \omega_0^2 \rho^2$ is the lateral confinement with frequency ω_0 , and in the Zeeman term $\sigma_x, \sigma_y, \sigma_z$ are the Pauli matrices. The analytical solution of H_0 yields the FD spectrum with energies $E_{n_1} = (2n_1 + |\mathbf{j}| + 1)\hbar\omega_0 + l\hbar\omega_c + 2 + g_B B = 2$, with effective

frequency $\omega_c = eB/(\hbar c)$; states are given in terms of associated Laguerre polynomials.¹⁶ The confinement magnetic and effective lengths are, respectively, $l_z = \sqrt{\hbar^2/(2m^*E)}$, $l_B = \sqrt{\hbar^2/(2m^*E)}$ and $l = \sqrt{\hbar^2/(2m^*E)}$.

The SIA SO term with coupling parameter is $H_{SIA} = \frac{\hbar}{2} (\nabla \times \mathbf{k})$, where the total confinement potential is $V(\mathbf{r}) = V(\rho) + V(z)$. One can then write $H_{SIA} = H_R + H_{SIA}^D$, where the diagonal contribution coming from the lateral confinement in cylindrical coordinates is $H_{SIA}^D = \frac{\hbar}{2} \frac{1}{L_z} L_z + \frac{\hbar^2}{2} \frac{x^2}{L_B^2}$, with the dimensional radial coordinate $x = \rho$, and $L_z = \hbar/\omega_c$.

The Rashba term coming from the perpendicular confinement field $dV=dz$ is

$$H_R = \frac{dV}{dz} [L_A + L_+ A_+], \quad (1)$$

where $L = \exp(i\phi)$, $\mathbf{k} = (k_x, k_y) = 2\pi/\lambda$, and operators $A = \partial/\partial x + L_z = x + x^2 = (2L_B^2)$.

In zincblende structures one should also consider the BIA SO bulk Hamiltonian.⁵ After averaging in the z-direction, due to quantization, one gets $H_{BIA} = k_x k_x k_y^2 + k_y k_y k_x^2 + k_z^2 [k_y k_y - k_x k_x] + k_z \hbar k_z i k_x^2 - k_y^2$, where \hbar is the coupling parameter, the resulting first (second) term is cubic (linear) in the in-plane momentum, and the last term is zero because $\hbar k_z i = 0$; also, $k_z^2 = (z_0)^2$, where z_0 is the z-direction confinement length. One may write the BIA SO term as $H_{BIA} = H_D^L + H_D^C$, where the linear Dresselhaus contribution is given by

$$H_D^L = i \frac{k_z^2}{L} [L_+ A_+ - L_A], \quad (2)$$

while the cubic contribution H_D^C can be expressed in terms of L^3 and L , and different powers in x , $\partial/\partial x$, and L_z .¹⁷ Notice that under a finite magnetic field, the matrix elements with L in H_D^C are non-hermitian, and one needs to symmetrize them;⁷ if the field is zero, this problem does not occur.¹³

For the electron-electron interaction H_{ee} , an expansion in Bessel functions for $j_1 - j_2$ is employed.¹⁷ The basis states are properly antisymmetrized, describing the unperturbed spin eigenstates.

The general form of the various SO terms in the Hamiltonian exhibit already interesting characteristics. For example, the magnetic field plays a role via its linear dependence in H_{SIA}^D , H_R , and H_D^L , or its B to B^3 dependence in H_D^C .¹⁷ Most interestingly, this form of the Hamiltonian yields selection rules explicitly, dictating which levels will be influenced by the SO effects. For example, at zero field the diagonal SIA term splits the levels according to the total angular momentum j . The Rashba term induces a set of anticrossings in the FD spectrum whenever $l = l = 1$ at finite field (due to the L term; mostly negative l 's are affected since their magnetic dispersions allow for crossings); the lowest anticrossing is

between $f_n; l; g = f_0; 0; g$ and $f_0; 1; +g$. The cubic BIA terms (with L^3) induce a set of anticrossings, which obey $l = 3$ and $l = 1$; the first one at low B -field involves the states $f_0; 1; g$ and $f_0; 2; +g$. Terms with L in H_D^L and H_D^C do not induce anticrossings, but rather split and shift the spectrum due to matrix elements with $l = 1 = 1$. Notice that the matrix elements between states with different n 's are in general non-zero, so that the full diagonalization involves mixings with various n -values.

Results. The sequence of FD states of H_0 starts at zero B -field with $f_n; l; g = f_0; 0; g$, followed by the degenerate set of $f_0; 1; g$ and $f_0; 1; g$.¹⁶ Spin and orbital degeneracies are broken by B and the states with negative l and positive l acquire lower energies because of the negative g -factor. The lowest energy level crossing is between states $f_0; 0; g$ and $f_0; 1; +g$, and the field where it occurs in the FD spectrum is

$$B_C^0 = \frac{\hbar \omega_c}{B} \sqrt{\frac{\hbar^2}{2m^*E} \frac{1}{\hbar^2 \omega_c^2 (2m^*E)^2}}, \quad (3)$$

where $\hbar \omega_c = m^* \omega_c$. The moderate value of B_C^0 is a direct consequence of the large ω_c in InSb.¹⁴ For GaAs ($\omega_c = 0.44$, $m^* = 0.067$), for example, this level crossing appears only at $B_C^{\text{GaAs}} = 9.4$ T for a much smaller confinement, $\hbar^2/2m^*E = 2$ meV, and in the region where Landau levels are well defined. Weaker confinement (smaller l) shifts this crossing to lower fields. Notice that for $g < 0$, H_R mixes these states (and H_D^L shifts the crossing to higher fields). For $g > 0$ it is H_D^L that would produce relatively stronger level anticrossings (and H_R would only shift the spectrum weakly), and it would then be absent in non-zincblende materials like silicon.

The energy spectrum for InSb QDs with typical characteristics,¹⁴ and for the full Hamiltonian is presented in Fig. 1A vs. B -field. The spectrum is obtained by direct diagonalization using a FD basis with $n = 4$ (or ten energy shells'), i.e. 110 basis states. We have studied the progressive changes to the FD levels when including different SO terms in H .

The diagonal H_{SIA}^D term shifts energies but does not change appreciably the position of the first crossing (3), shown by the dotted lines in Fig. 1A at 2.6 T. The energy shifts induce two new crossings at low fields (inset d), since the SO orders states according to their total angular momentum $j = 1 + s$; the highest (lowest) state at zero field has $j = 3 = 2$ ($l = 2$) in the second shell. At about 0.2 T one recovers the normal sequence of states: $f_0; 1; +g, f_0; 1; g, f_0; 1; +g, f_0; 1; g$. This competition between SO and magnetic field is similar to the Zeeman and Paschen-Back regimes in atoms.¹⁸ We should note that this level ordering is observed in [12].

The non-diagonal Rashba contribution H_R introduces strong state mixing for any value of the parameter whenever FD levels with $l = l = 1$ cross. This mixing converts the crossings at B_C^0 to clear anticrossings. Higher levels which satisfy these selection rules also anticross at nearly the same field. The field-width and

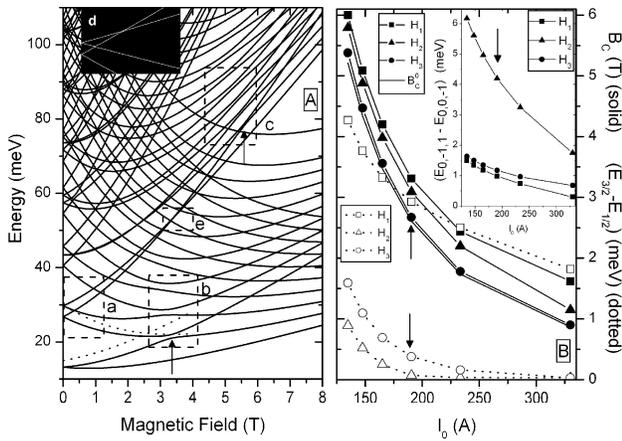


FIG. 1: A: Full Hamiltonian H spectrum vs. B: eld for InSb QD as in [14]. H highlights in dashed boxes: a shows zero- eld splitting in second shell (affected mostly by BIA SO terms), and crossing at about 0.3T; compare with inset d with only SIA terms and two crossings at 0.02 and 0.06T, and much smaller zero- eld splitting. Second crossing for this shell in full H is at 3.4T (e box). b and c indicate anticrossings (AC) induced by Rashba term with $l = 1$; first AC (arrow) in b involves states $f_0; 0$; g and $f_0; 1$; $+g$ ($f_0; 1$; g and $f_1; 0$; $+g$ in c). Dotted lines indicate FD levels crossing at 2.6T. B: Lateral size dependence. Dotted lines: SO zero- eld splitting in a box on left panel. Solid lines: B_C eld of first AC in b box on left panel; inset shows splitting at that AC. Arrows at 190Å show QD size for spectrum in A. H_1 curves (squares) use [14]; H_2 (triangles) and H_3 (circles) use same parameters but four times stronger Rashba eld (H_2) or twice as large z_0 (H_3). Both cases increase relative strength of SIA terms. Solid line with no symbol shows B_C^0 in (3).

energy-amplitude (or level splitting) of the mixing is dictated by the value of α , while the value of B_C where the anticrossing occurs is nearly unaffected by α .

The cubic Dresselhaus contribution H_D^C induces anticrossings (via L^3) and zero- eld splittings (L) in the FD spectrum. The splittings are much smaller than those induced by the Rashba term and practically unnoticeable in the spectrum, reflecting the smallness of the E_D^C for these parameters.¹⁴ For the linear BIA contribution, however, the L terms in H_D^L have a much bigger impact on the zero- eld splittings, which can in principle be 'tuned' by changing the effective z-size, z_0 . H_D^L alone induces such a strong mixing at low elds that one cannot identify the two Zeeman and Paschen-Back regimes.

Notice in the full spectrum of H (Fig. 1A) that the first group of anticrossings (for $n = 0$ levels) induced by H_R is shifted to higher eld due mostly to H_D^L , so that $B_C \neq B_C^0$! $B_C \approx 3.3T$ (box b and lower arrow). The set of anticrossings at $5.5T$ is also due to H_R and arises from the $n = 1$ level manifold (box c and upper arrow). At low eld, only a single crossing in the second shell at $0.3T$ is

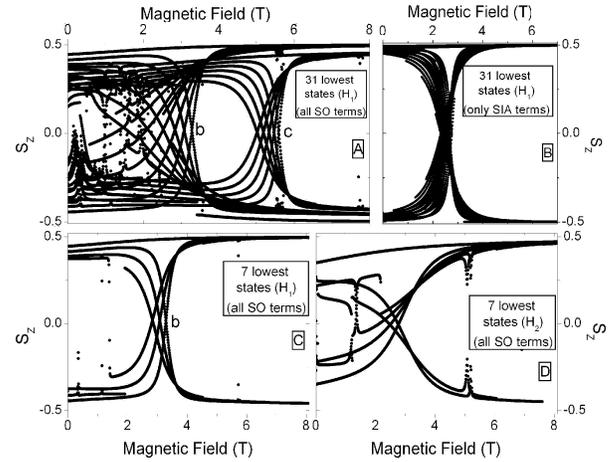


FIG. 2: A: Spin z-component vs. B: eld for lowest 31 states; b and c labels refer to boxes in Fig. 1A. Higher energy anticrossings in each set are shifted to lower elds. If only SIA terms are considered (panel B), all spin mixing occurs at eld $B_C \approx 2.6T$. C: S_z for lowest 7 states; full spin mixing at anticrossing. D: dot with Rashba eld 4 times stronger (H_1 and H_2 defined as in Fig. 1). Increasing SIA SO produces stronger mixing.

present and dominated by H_D^L (box a; compare with inset d and notice second crossing in box e). The sequence of the first excited levels at zero eld is $j = 3=2$ ($l=2$) for higher (lower) energy, while at higher energies both SIA and BIA terms cooperate to produce anticrossings (not visible at the resolution in Fig. 1A).

Figure 2 illustrates the importance of the level anticrossings on the spin, as the expectation value of S_z for each state is plotted vs. B. Figs. 2A and B include all states with $E \leq 80$ meV (for full SO and only SIA terms, respectively), while Figs. 2C and D focus only on the lowest seven levels. Although a large majority of states have S_z close to $l=2$, as one expects for pure states, there are significant deviations. The various SO terms mix levels close to accidental degeneracy points in the FD spectrum and produce the large deviations seen in the figure. 2C shows how H_R produces an intrinsic (i.e., no phonon-assisted) total collapse of the spin number for the low energy states in the QD. Although the ground state is nearly pure ($S_z \approx 1=2$, and more so at higher B), the first few excited states totally mix at $B_C \approx 3.3T$. 2D shows how a stronger Rashba eld ($dV=dz = 2 \times 10^3$ eV/Å) greatly widens the mixing region and lowers $B_C \approx 2.8T$.

One can further appreciate the intricate balance of SO terms under a magnetic eld. We analyze how various quantities are affected by changes in the lateral and vertical sizes, l_0 and z_0 , or the Rashba eld $dV=dz$, as shown on Fig. 1B. The zero- eld splitting (dotted lines) is dominated by the linear BIA contribution for any value of l_0 here. Increasing z_0 strongly reduces the splittings because the Dresselhaus contribution weakens; the reduction is even more drastic if one increases $dV=dz$, which

makes the H_R contribution bigger and can then cancel or suppress better the splitting produced by H_{SIA}^D . Some authors have considered the possibility of tuning such SO terms to produce total cancellation of the zero-field splitting, although considering only H_R and H_D^L .⁴ However, one also has to take into account H_{SIA}^D and H_D^C contributions, which may be important (the zero-field cancellation occurs at values of z_0 or Rashba field about ten percent smaller than with only the former terms). One should notice, in any event, that this change in parameters only eliminates the zero-field splitting but not the anticrossing at finite field, and measurement of both quantities on the same sample could yield information on the relative strength of the parameters.

The anticrossing field B_C (solid lines/symbols) decreases with QD size, roughly according to (3), $B_C^0 \propto \frac{1}{l_0} \propto \frac{1}{l_0}$. A finite z_0 slightly increases B_C , but the BIA contribution considerably upshifts it, as mentioned above. Increasing z_0 or $dV=dz$ decreases B_C . At $l_0 = 320\text{\AA}$ ($\sim l_0 = 5\text{m eV}$), $B_C = 1.6\text{T}$, while it shifts to 1.15T if $dV=dz$ is four times larger or to 0.85T if z_0 is doubled, both cases decreasing the BIA contribution. These values are comparable to those in [9] without including BIA terms (adjusting for differences in system parameter values). Anticrossings at such low fields may be interesting for applications due to easier access.

The energy splitting at B_C (inset in Fig. 1B), has a contribution from the Rashba term for any dot size considered, but the BIA reduces the splitting substantially. If z_0 is changed from 40 to 80Å the splitting is enhanced slightly, but larger z_0 produces no significant changes. However, the splitting is drastically enhanced if one increases the Rashba field. Here, the splitting goes from 1 to 4.2meV if the interface field is increased fourfold.

Figure 3 illustrates the corresponding level structure for two electrons in the QD (full Hamiltonian $H + H_{ee}$; dashed lines show $H_0 + H_{ee}$, the non-SO case). The repulsive interaction shifts the ground state upwards by $\sim 5\text{m eV}$, and the exchange shifts the triplet down by 2meV. Most interestingly, the SO interaction introduces a strong mixing of the singlet and triplet transition at $B \sim 2.7\text{T}$. The fact that the mixing occurs at relatively low field makes that a possibly useful transition for the implementation of quantum computing devices. Moreover, the splitting will also be apparent in the FIR response of QDs, allowing the determination of the various SO coupling strengths.

We have shown that inclusion of all SO terms is essential in order to obtain a complete picture of the level structure in narrow-gap QDs. The combination of strong SO couplings and large (and negative) g factor introduces strong intrinsic mixing of the low excitations for the single-particle spectrum. Consequently, the two-particle spectrum exhibits strong singlet-triplet coupling at moderate fields, with significant experimental consequences. Observation of FIR mode magnetic dispersion would allow the direct determination of coupling constants.

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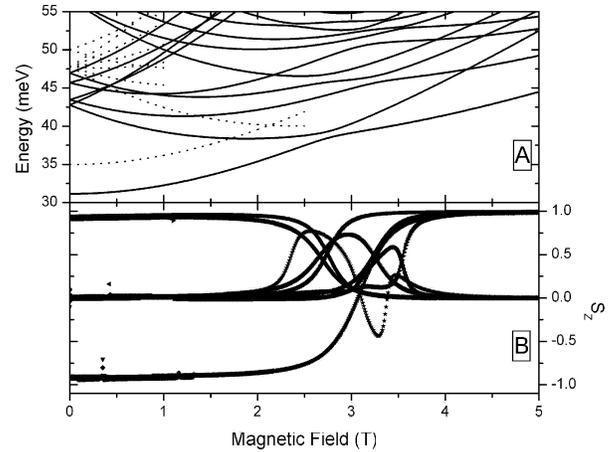


FIG. 3: A: Two particle spectrum vs. B field for full Hamiltonian $H + H_{ee}$ (basis included 190 states, only lowest levels shown). With no SO (dotted lines) and at $B = 0$, ground state is a singlet ($fL; Sg = f0; 0g$) at 35m eV while first (second) excited state is a triplet ($f 1; 1g$ and $f 1; 0g$) at 48m eV (singlet ($f 1; 0g$) at 50m eV). SO acts against electron-electron interaction, as levels are shifted back to energies close to non-interacting case. Lowest anticrossing at $B \sim 2.7\text{T}$ is between singlet ground state $f0; 0g$ and lowest excited triplet state $f 1; 1g$; SO introduces coupling between the singlet and triplet states with direct consequences for QD ground state. B: Spin S_z for the nine lowest states of the two particle QD. Strong mixing induced by SO interaction appears in all states $B \sim 3\text{T}$.

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